Electronic Stripes and Transport Properties in Borophene Heterostructures

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We performed a theoretical investigation of the structural and electronic properties of (i) pristine, and (ii) superlattice structures of borophene. In (i), by combining first-principles calculations, based on the density functional theory (DFT), and simulations of the X-ray Absorption Near-Edge Structure (XANES) we present a comprehensive picture connecting the atomic arrangement of borophene and the X-ray absorption spectra. Once we have characterized the electronic properties of the pristine systems, we next examined the electronic confinement effects in 2D borophene superlattices (BSLs) [(ii)]. Here, the BSL structures were made by attaching laterally two different structural phases of borophene. The energetic stability, and the electronic properties of those BSLs were examined based on total energy DFT calculations. We find a highly anisotropic electronic structure, characterized by the electronic confinement effects, and the formation of metallic channels along the superlattices. Combining DFT and the Landauer-Buttiker formalism, we investigate the electronic transport properties in the BSLs. Our results of the transmission probability reveal that the electronic transport is ruled by π or a combination of π and σ transmission channels, depending on the atomic arrangement and periodicity of the superlattices. Finally we show that there is huge magnification on the directional dependence of the electronic transport properties in BSLs, in comparison with the pristine borophene phase. Those findings indicate that BSLs are quite interesting systems in order to design conductive nanoribbons in a 2D platform.

I. INTRODUCTION

Since the breakthrough of graphene in 2004, the synthesis of two dimensional (2D) materials reached the state of the art. The formation of the honeycomb lattice in graphene is dictated by the C-\(sp^2\) hybridization of the carbon atoms, favoring the formation of two dimensional systems. Such an electronic/orbital “ingredient” is also present in boron atoms (B-\(sp^2\)), and thus pointing out the possibility of synthesis of 2D boron systems.

Indeed, there are several theoretical studies, based on first-principles calculations, predicting 2D systems composed by boron atoms. Meanwhile, in a seminal work, Mannix et al. obtained 2D boron sheets (borophene) on the Ag(111) surface; and few months latter, Feng et al. synthesized two new different structural phases of borophene on the same substrate. The former boron 2D structure is characterized by a buckled geometry where the boron atoms are six-fold coordinated; while the latter presents a planar geometry with the presence boron vacancies, giving rise to six-, five-, and four-fold boron coordinations. In a very recent work, Rajan et al. successfully performed a large scale synthesis of free-standing borophene sheets, which is a quite important step towards the design layered devices based on borophene.

The combination of materials with distinct electronic properties has been one of the most promising route to the design new electronic devices. Such a material engineering began with 3D semiconductor heterostructures, like (GaAs)\(_m\)/AlAs\(_n\) superlattices (SLs). The electronic properties of those hybrid systems are mostly ruled by the intrinsic characteristics of the pristine materials (e.g. GaAs and AlAs), and their respective size/periodicity (m and n) within the SL. Upon the further progress on the growth processes, 2D lateral heterostructures have been successfully synthesized, like WS\(_2\)/MoS\(_2\), and 2H-MoS\(_2\)/1T-MoS\(_2\). The former is a 2D heterostructure composed by different materials (WS\(_2\) and MoS\(_2\)), while in the latter we have a single material but with different structural phases (2H and 1T).

Taking advantage of the polymorphism of 2D boron lattices, Liu et al. built-up borophene heterostructures composed by self-assembled periodic structures of linear stripes with different atomic arrangements. In particular, borophene phases with hollow hexagons concentration (\(\eta\)) of 1/6 and 1/5, so called S1 and S2. As depicted in Fig. 1, each borophene phase is characterized by different electronic structures and density of states near the Fermi level, which can be exploited in order to design new electronic devices in 2D platforms. For instance, promoting the electronic confinement, and the directional dependence of the electronic transport properties.

In this work, based on the first-principles density functional theory (DFT) calculations, we performed a theoretical study of (i) pristine borophene sheets, and (ii) borophene heteostructures composed by combinations of S0, S1 and S2 phases. In (i), based on the DFT calculations, and simulations of the X-ray absorption spectra (XAS) we present a detailed study of the electronic/structural properties based on the near edge X-ray absorption results. Once we characterized the pristine systems, in (ii) we investigate the energetic stability,
the electronic confinement and transport properties in borophene heterostructures. In our study, we considered periodic combinations of the different structural phases, viz.: \( S_0/n/S_1n, S_0/m/S_1m/S_2m \), forming borophene superlattices (BSLs) with \( m/n \) periodicities. We found that the relative width of the borophene stripes rules the localization of the electronic states and the metallic bands. Our electronic transport calculation, performed within the DFT and the Landauer-Büttiker formalisms, reveals that the electronic currents along the \( S1/S2 \) BSLs are localized and strongly anisotropic.

II. METHOD

The calculations were performed within the density functional theory, where the exchange-correlation term was described within the generalized gradient approximation as proposed by Perdew, Burke and Ernzerhof (GGA-PBE). The calculations of the equilibrium geometries, total energies, and the electronic band structures were done by using the VASP code.27,28 The Kohn-Sham orbitals are expanded in a plane wave basis set with an energy cutoff of 400 eV. The 2D Brillouin Zone (BZ) is sampled according to the Monkhorst-Pack method, using a gamma-centered \( 12 \times 12 \times 1 \) mesh. The electron-ion interactions are taken into account using the Projector Augmented Wave (PAW) method.30 All geometries have been relaxed until atomic forces were lower than 0.025 eV/Å.

The boron K-edge X-ray absorption near-edge structure (XANES) spectra were simulated using the theoretical approach implemented in the XSpectra code,31-33 supplied with QUANTUM ESPRESSO.34 We have used ultrasoft pseudopotentials, where in order to describe the K-edge spectra, we built a pseudopotential with a core hole in the \( 1s \) orbital, and the all electron wave function were recovered by using the GIPAW approach.35

The electronic transport calculations was explored using the non-equilibrium Green’s function (NEGF) formalism using the DFT Hamiltonian as implemented in TranSiesta.36,37 The total transmission probability of electrons with energy \( E(T(E)) \) from the left electrode to reach the right electrode passing through the scattering region is given by,

\[
T(E) = T_R \left( \Gamma_R(E,V) G^R(E,V) \Gamma_L(E,V) G^A(E,V) \right),
\]

where \( \Gamma_{L,R}(E,V) \) is the coupling with the left and right electrodes and \( G^{R,A} \) is the retarded (advanced) Green function matrix of the scattering region. The current \( I \) is evaluated by using Landauer-Büttiker formula,38,39

\[
I(V) = \frac{2e}{\hbar} \int T(E,V) \left[ f(E - \mu_L) - f(E - \mu_R) \right] dE,
\]

where \( f(\epsilon) \) is the Fermi-Dirac distribution for energy \( \epsilon \) and \( \mu_{L,R} \) is the electrochemical potential of left (right) electrodes.

III. RESULTS AND DISCUSSIONS

![Figure 1](image)

**FIG. 1.** Electronic structure, and wave models of the pristine borophene sheets with different vacancy concentration \( \eta \). (a) \( S0 (\eta = 0) \), (b) \( S1 (\eta = 1/6) \), and (c) \( S2 (\eta = 1/5) \); and the projected density of states near de Fermi level, \( E_F \pm 0.1 \) eV. The isosurfaces in (a2) and (b2) are equal to 0.0025 e/Å³, and in (c2) 0.005 e/Å³.

A. Pristine sheets

In Fig.1 we present the structural models and the electronic bands structures of pristine borophene \( S0 \) [Fig. (1a)], \( S1 \) [Fig. (1b)], and \( S2 \) [Fig. (1c)] phases. In \( S0 \) the B atoms are six-fold coordinated, and present a buckled geometry giving rise to two layers of boron atoms with a vertical distance (z direction) of 0.87 Å. The electronic band structure of \( S0 \) is highly anisotropic, characterized by the formation of metallic bands for wave vectors along the \( \Gamma-X \) and \( Y-S \) directions [Fig. 1(a1)].7 In Fig. 1(a2) we present projected the electronic density of states near de Fermi level, \( E_F \pm 0.1 \) eV, where we can identify the wave function overlap along the \( z \)-direction. In a recent work, we verified that the electronic transport properties in \( S0 \) are characterized by a strong directional dependence.23 Upon the presence of vacancies in \( S0 \), as presented in \( S1 \) and \( S2 \), the vertical buckling has been suppressed.8 The planar boron sheets, with four- five- and six-fold coordinated B atoms, are characterized by a density of hollow hexagons \( \eta \) of 1/6 and 1/5, respectively.40 The energetic stability of those pristine systems was examined through the calculation of the cohesive energy \( (E_c) \).
We found $E^*$ of 6.21, 6.25, and 6.27 eV/atom for S0, S1 and S2 phases. The energetic preference of S1 and S2, compared with S0 is in agreement with the previous first-principles results.\textsuperscript{5,7,8}

The metallic character of borophene in S1 and S2 phases has been kept, Figs. 1(b1) and (c1), however, compared with S0, the electronic anisotropy is somewhat dimmed. We find that the metallic bands of S1 are mostly composed by the B-2$p_z$ and -2$p_x$ orbitals localized on the four- and five-fold coordinated B atoms. Meanwhile, in S2 the formation of the metallic bands along the Γ-Y and S-X directions is dictated by a combination of $\sigma$- (B-2$p_y$) and π-orbitals (B-2$p_z$).

In order to get some insight into the structural and electronic features of the borophene sheets, we simulate the boron K-edge X-ray absorption near-edge structure (XANES). By considering the polarization vector perpendicular to the borophene sheet ($\hat{\epsilon}_\perp$), we have examined the main features associated with the B-1$s \rightarrow \pi^*$ transitions.

The boron atoms in S0, S1 and S2 are characterized by different bonding geometries and coordinations. (i) In S0 and S1 we have six-fold coordinated boron atoms. The former presents a buckled geometry, giving rise to boron lines along the $x$-direction [Fig. 1(a2)], while S1 exhibits a planar geometry, where the six-fold boron atoms are separated by boron vacancy lines, Fig. 1(b2). As shown in Figs. 2(a1) and (a2), those structural differences can be identified at the near-edge absorption interval; namely, the B-1$s \rightarrow \pi^*$ absorption peak in S0 present a larger energy dispersion [$\Delta$ in Fig. 2(a1)] in comparison with its counterpart in S1 [Fig. 2(a2)]. Thus, indicating that the presence of vacancy lines, and the planar geometry of S1 result in a more localized $\pi^*$ states in comparison with the buckled S0 phase. (ii) In S1 and S2 we have vacancies, five-fold, and four-fold coordinated boron atoms, where in S1 the hexagonal boron structures are separated by vacancy lines, while in S2 we have zigzag stripes of boron-dimers separated by vacancy lines. As shown in Figs. 1(b2) and (c2), the electronic density of states of S1 and S2, near the Fermi level, present different pictures. The hybridization in S1 somewhat mimic the one present in graphene, while in S2 there is charge density overlap along the zigzag stripes of B-dimers. Our XAS results (at the near-edge region) for the five- and four-fold coordinated boron atoms of S1 [shaded regions in Figs. 2(b1) and (c1)] are characterized by a more intense B-1$s \rightarrow \pi^*$ transition when compared with the ones in S2, [shaded regions in Figs. 2(b2) and (c2)]. Thus, indicating that the B-1$s \rightarrow \pi^*$ transition becomes more (less) intense upon the presence hexagonal (dimer) structures in S1 (S2).
FIG. 4. Structural models and the electronic density of states within $E_F \pm 0.1 \text{ eV}$, of S1$_4$/S2$_1$ (a1), S1$_2$/S2$_1$ (b1), S1$_2$/S2$_2$ (c1), and S1$_1$/S2$_4$ (d1) BSLs. Electronic structure and the projection of the energy bands on S1$_4$ (a2) and S2$_1$ (a3); S1$_2$ (b2) and S2$_1$ (b3); S1$_2$ (c2) and S2$_2$ (c3); S1$_1$ (c2) and S2$_1$ (c3). Isosurfaces of 0.003 e/Å$^3$ in (a) and (d); and 0.0015 e/Å$^3$ in (b) and (c).

B. 2D boron superlattices

Motivated by the recent advances on the synthesis of 2D heterostructures,$^{22}$ and the theoretically proposed electronic localization upon the presence of defects in borophene,$^{42}$ we examined the structural and electronic properties of lateral borophene heterostructures. In particular, we have considered 2D boron superlattices (BSLs) combining the different structural phases of borophene, with m/n periodicities, separated by zigzag edges. For instance, in S0$_1$/S1$_7$ (m=1/n=6) we have one periodic unit cell of S0 separated by six periodic unit cells of S1. Fig. 3(a1). The energetic stability of those BSLs was inferred by the calculation of the cohesive energies ($E^c$), where we found $E^c$ of 6.26 eV/atom. Our results of $E^c$, summarized in Table I, show that the cohesive energies of the other BSLs are practically the same when compared with the ones of the pristine phases. Thus, supporting the energetic stability of those boron superlattices.

Next we examine the electronic properties of the BSLs as a function of the relative width (m/n) of each structural phase. In the S0$_1$/S1$_7$ BSL the electronic states near the Fermi level, $E_F \pm 0.1 \text{ eV}$, are mainly localized on the S1 stripes [Fig. 3(a1)], characterized by the graphene-like $\pi$-hybridizations along the four- and five-fold coordinated boron atoms along the inner sites of S1. The localization of the electronic states can be also identified through the projection of the energy bands on S0 and S1, Figs. 3(a2) and (a3), respectively; where it is noticeable the most of metallic bands lying on S1. Such a localization of the electronic states near the Fermi level, and the electronic separation of the metallic bands have been also observed in S0$_1$/S2$_4$, Fig. 3(b). Here, the electronic states are predominantly localized along the S2 stripes. However, as shown in Fig. 3(b3), in addition to the $\pi$ orbitals, we find that the $\sigma$-hybridizations also contribute

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FIG. 5. Schematic representation of the setup used for the transport calculations along the S1m/S2n BSLs. Herein, we have calculated the electronic transport for different S1m/S2n combinations, such as: S1\textsuperscript{4}/S2\textsuperscript{1}, S1\textsuperscript{2}/S2\textsuperscript{1}, S1\textsuperscript{2}/S2\textsuperscript{2}, and S1\textsuperscript{1}/S2\textsuperscript{4}.

to the formation of the metallic bands.

The large number of possible structural combinations to build up heterostructures, based on borophene, is an interesting degree of freedom in order to control/design the electronic properties in 2D systems. Very recently, borophene heterostructures composed by S1 and S2 phases have been successfully synthesized,\textsuperscript{22} where the authors identified S1/S2 periodic assemblies with different relative concentrations. Here we will examine the S1\textsuperscript{m}/S2\textsuperscript{n} BSLs, with m/n of 4/1, 2/1, 2/2, and 1/4, depicted in Fig. 4. At the equilibrium geometry, (i) the planar structure has been preserved, and (ii) the S1/S2 zigzag interface boron atoms are neatly arranged, where the B–B bond lengths and angles are practically the same compared with the ones the pristine structures. The energetic stability was examined by the calculation of the cohesive energy, where we found $E^c$ between 6.26 and 6.27 eV/atom, Table I, which are close to the ones of the isolated S1 and S2 phases.

In S1\textsuperscript{4}/S2\textsuperscript{1}, the electronic states within $E_F \pm 0.1$ eV are mostly confined in S1 ruled by the S2 stripes. There is a charge density overlap along the S1 stripes, giving rise to metallic bands for wave vectors parallel to the ΓY and SX directions, Fig. 4(a2) and (a3). Those metallic bands are predominantly composed by the B–2$p_z$ orbitals lying on the four- and five-fold coordinated boron atoms of S1. Meanwhile, the projection of the energy bands on S2 reveals contributions from B–2$p_z$ and -2$p_y$ orbitals to the formation of the metallic bands. On the other hand, the electronic states with wave vector perpendicular to the S1/S2 interface, namely ΓX and YS directions, are characterized by dispersionless energy bands localized mainly on S1.

Reducing the width of S1, S1\textsuperscript{4}/S2\textsuperscript{1} → S1\textsuperscript{2}/S2\textsuperscript{1}, the distribution of the electronic density of states near the Fermi level, on the S1 and S2 stripes, becomes almost equivalent, however they present different features, Fig. 4(b). The metallic bands are characterized by π-hybridization through S1, while in S2 we have both, i.e. π- and σ-hybridizations (B–2$p_y$), with a major contribution from the latter forming zigzag B-dimers lines. Keeping the width of S1, and increasing S2, S1\textsuperscript{2}/S2\textsuperscript{1} → S1\textsuperscript{2}/S2\textsuperscript{2}, we find that the electronic states near the Fermi level become more localized on S2, in particular on the four-fold coordinated boron atoms, as shown in Fig 4(c1). Indeed, the π- and σ-hybridizations along the S2 stripes have been strengthened, giving rise to metallic bands along the ΓY and SX directions, concomitantly there is a reduction of the electronic contribution from S1. Finally, upon further reduction of S1 and increase of S2, S1\textsuperscript{2}/S2\textsuperscript{2} → S1\textsuperscript{1}/S2\textsuperscript{4}, we find that there is a noticeable change on the electronic distribution along S2, where the wave function overlap between the B–2$p_y$ orbitals becomes more intense, strengthening the σ-hybridizations and the orbital localization along S2, characterized by zigzag stripes of B-dimers [Fig. 4(d2) and (d3)].

Focusing on the electronic transport properties in 2D systems, the “directional dependence”, and the “role of intrinsic line defects” are important issues that have been addressed in recent studies.\textsuperscript{23,25,43,44} Here, we will discuss the role of the confinement/localization on the electronic transport properties along the S1/S2 BSLs. We have
examined the electronic transport (i) along the superlati-
cicates, i.e. along the $y$-direction, as shown in Fig. 5; and
(ii) perpendicularly to the interface, $x$-direction. In (ii)
we obtained nearly zero transmission probabilities, thus
indicating that the electronic transport in BSLS presents
a strong directional dependence.

In Fig. 6(a) we present the transmission probability ($T$)
along the S1/S2 stripes ($T_{x,y}^{S1}$), where we show that $T_{x,y}^{S1}$
lies between the transmission probabilities of the pristine
S1 ($T_{y}^{S1}$) and S2 ($T_{y}^{S2}$) phases, namely $T_{y}^{S1} < T_{x,y}^{S1} < T_{y}^{S2}$,
for an energy interval of $E_F \pm 0.5$ eV. Based upon the
projected energy bands, Figs. 4(a2) and (a3), we can infer
that the larger values of $T_{x,y}^{S1}$, compared with $T_{y}^{S1}$, can
be attributed to the strengthening of the $\pi$-hybridization
along the inner sites of S1, in addition with the metallic
bands along S2. On the other hand, the reduction of $T_{x,y}^{S1}$
below the Fermi level, indicated by an arrow in Fig. 6(a),
is correlated with the formation of localized (B-$2p_x$)
occupied states just below the Fermi level. That is, there
is an interaction between the propagating waves and the
electronic states with wave vectors along the $y$ direction,
Figs. 4(a2) and (a3), localized in S1 and S2.

By reducing the width of S1, S1$_4$/S2$_1 \rightarrow$ S1$_2$/S2$_1$, we
find (i) a reduction of the transmission probability,
namely $T_{y}^{S1} < T_{y}^{S2}$, (ii) being larger than $T_{y}^{S1}$ only near
the Fermi level [(i) and (ii) are indicated in Fig. 6(b)].
In fact, these features are in agreement with the reduction
on the density of (B-$2p_x$) metallic bands along S1,
as shown in Fig. 4(b). Meanwhile, presence of the localized
states, along the SY and XT directions, gives rise to the
transmission valley below the Fermi level, indicate as
(iii) in Fig. 6(b). Increasing the width of the S2 re-
gression, S1$_2$/S2$_1 \rightarrow$ S1$_2$/S2$_2$, the features (i)–(iii) described
above are are somewhat preserved. However, in S1$_2$/S2$_2$
the contribution of B-$2p_y$ orbitals, localized on S2, be-
comes dominant to the formation of transport channels

IV. SUMMARY AND CONCLUSIONS

Based on first-principles DFT calculations we have ex-
amined the electronic and structural properties of the re-
cently synthesized (i) pristine borophene sheets with dif-
ferent vacancy concentrations, $\eta$=0, 1/6, and 1/5, namely
S0, S1 and S2; and (ii) borophene superlattices (BSLs)
composed by combinations of those structural phases.

In (i), once we confirmed the metallic character of
the pristine systems, through simulations of X-ray Abs-
sorption Near-Edge Structure (XANES) we unveil the
connection between the electronic properties and the
atomic arrangement of borophene S0, S1, and S2 phases.
The near edge spectra of the six-fold coordinated boron
atoms, present in S0 and S1, exhibit a more localized
feature in the latter. The presence of vacancies in S1 re-
duces the wave function overlap of the $\pi^*$ orbitals. Five-
and four-fold coordinated boron atoms are present in S1 and S2. In S1, they are arranged in hexagonal stripes,
separated by vacancy lines, favoring the B-1s $\rightarrow$ $\pi^*$
transitions. Such a transition is weakened in S2. In S2, the
five- and four-fold coordinated boron atoms form zigzag
B-dimer stripes separated by vacancy lines. In this case,
we found a strengthening of the B-1s $\rightarrow$ $\sigma^*$ transition.
Those features, identified by our XANES results, provide
a structural fingerprint for the S0, S1, and S2 phases of
borophene.
energetic stability of the BSLs was inferred through the calculation of the cohesion energy, where we found practically the same values of their pristine counterparts. Focusing on the electronic properties, we found that BSLs composed by wider stripes of S1 (S2) separated by a single stripe of S0, e.g. S01/S15 (S01/S24), promote the separation/localization of the electronic states near the Fermi level. Further projection of the energy bands revealed the localization of the metallic bands along the S1 (S2) stripes, giving rise to metallic S1 (S2) ribbons separated by S0 stripes. Such a separation/localization of the electronic states also takes place in S1/S2 BSLs, where the localization of the metallic bands can be tuned by the relative width of the borophene ribbons. For instance, in S14/S2, (S1/S2) we find the most of metallic states, composed by B-2p_z (B-2p_y and B-2p_x) orbitals, localized along S1 (S2). Those findings indicate that the “directional dependence” on the transport properties will be strengthened in BSLs, where in S1/S2 the transmission channels will be ruled by π-orbitals (combination of π and σ orbitals) for S1 (S2). Such a “directional dependence” on the transport properties was verified through the calculation of the transmission probabilities in S1/S2 BSLs. Indeed, we found a nearly zero electronic transmission perpendicularly to the S1 and S2 stripes. On the other hand, along the S1/S2 stripes the transmission coefficients exhibit a reduction within an energy window of 0.2 eV below the Fermi level. Since the propagating waves are scattered by localized states lying at the S1–S2 interface region. The I–V results show that the current densities of the S1/S2 BSLs are lower (higher) than that of pristine S2 (S1), being proportional to the width of the S2 phase in the superlattice. Those findings indicate that BSLs, based on a combination of different structural phases borophene, are quite interesting systems in order to design conductive nanoribbons in a 2D platform.

V. ACKNOWLEDGMENTS

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Hole density ($\eta$) is defined as the ratio between the number of hexagon holes and the total number of atoms in the original (pristine) triangular lattice.

$E^c$ is defined as the total energy difference between the borophene sheet or superlattice and the isolated B atoms.


